

## NPN Silicon Epitaxial Planar Transistor

for high voltage and high speed switching applications



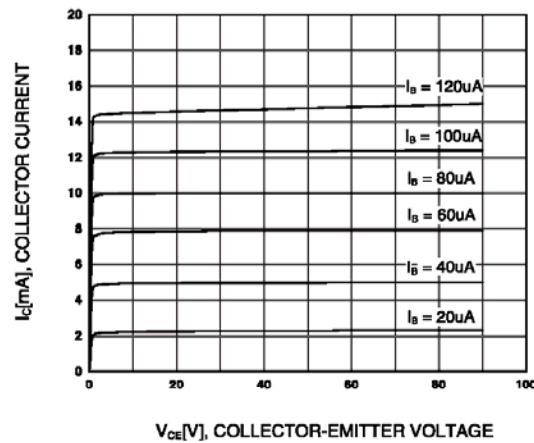
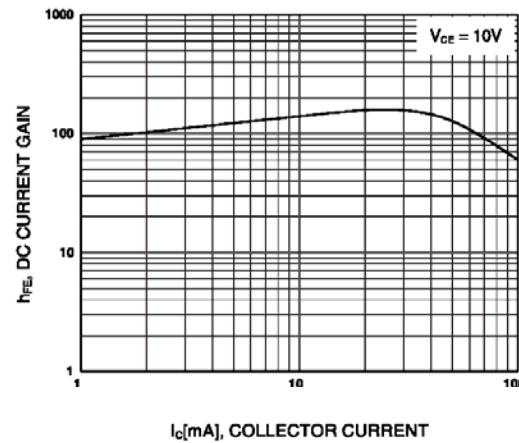
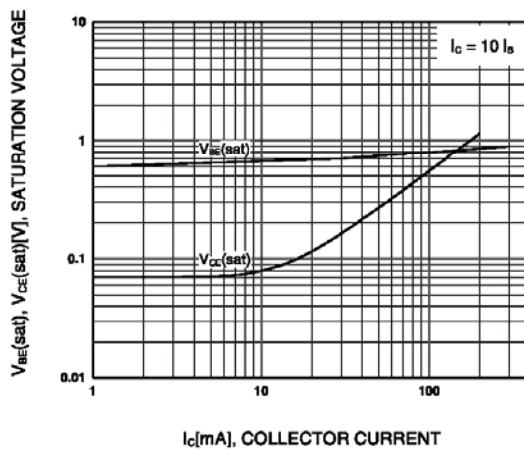
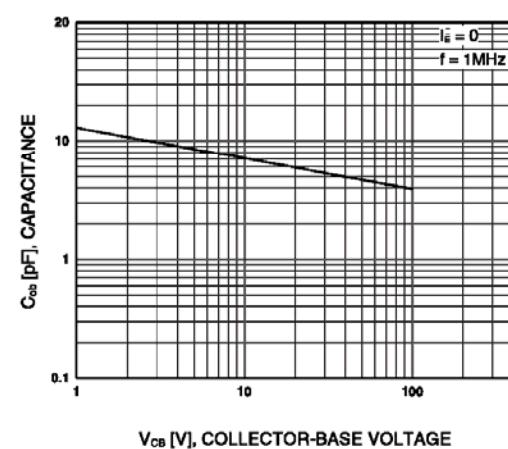
1. Emitter 2. Collector 3. Base  
TO-92 Plastic Package

Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	500	V
Collector Emitter Voltage	$V_{CEO}$	400	V
Emitter Base Voltage	$V_{EBO}$	9	V
Collector Current (DC)	$I_C$	0.3	A
Total Power Dissipation	$P_{tot}$	0.75	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

Characteristics at  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 10 \text{ V}$ , $I_C = 0.25 \text{ mA}$ at $V_{CE} = 20 \text{ V}$ , $I_C = 20 \text{ mA}$	$h_{FE}$ $h_{FE}$	5 10	- 40	- -
Collector Base Cutoff Current at $V_{CB} = 500 \text{ V}$	$I_{CBO}$	-	100	$\mu\text{A}$
Collector Emitter Cutoff Current at $V_{CE} = 400 \text{ V}$	$I_{CEO}$	-	200	$\mu\text{A}$
Emitter Base Cutoff Current at $V_{EB} = 9 \text{ V}$	$I_{EBO}$	-	100	$\mu\text{A}$
Collector Base Breakdown Voltage at $I_C = 100 \mu\text{A}$	$V_{(BR)CBO}$	500	-	V
Collector Emitter Breakdown Voltage at $I_C = 1 \text{ mA}$	$V_{(BR)CEO}$	400	-	V
Emitter Base Breakdown Voltage at $I_E = 100 \mu\text{A}$	$V_{(BR)EBO}$	9	-	V
Collector Emitter Saturation Voltage at $I_C = 50 \text{ mA}$ , $I_B = 10 \text{ mA}$	$V_{CE(sat)}$	-	0.5	V
Base Emitter Saturation Voltage at $I_C = 50 \text{ mA}$ , $I_B = 10 \text{ mA}$	$V_{BE(sat)}$	-	1.2	V
Transition Frequency at $V_{CE} = 20 \text{ V}$ , $I_C = 20 \text{ mA}$ , $f = 1 \text{ MHz}$	$f_T$	8	-	MHz
Storage Time at UI9600, $I_C = 100 \text{ mA}$	$t_s$	-	3	$\mu\text{s}$
Fall Time at UI9600, $I_C = 100 \text{ mA}$	$t_f$	-	1	$\mu\text{s}$

**Figure 1. Static Characteristic****Figure 2. DC current Gain****Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage****Figure 4. Collector Output Capacitance**